Journal of Crystal Growth 92 (1988) 693–697
North-Holland, Amsterdam

AUTHOR INDEX

Ahmed, M.A., see Mousa 92 (1988) 259
Aina, O., M. Mattingly, S. Steinhauser, R. Mariella, Jr. and A. Melas, SIMS and photoluminescence evaluation of high purity InP grown by organometallic vapor phase epitaxy 92 (1988) 215
Akasaki, I., see Tanaka 92 (1988) 311
Amano, N., see Tanaka 92 (1988) 311
Ando, K., see Nomura 92 (1988) 682
Andreazza, P., F. Lefaucheux and B. Mutaftschiev, Nucleation in confined space: application to the crystallization in gels 92 (1988) 415
Andrews, R.N., F.R. Szofran and S.L. Lehoczky, Growth and characterization of $Hg_{1-x}Cd_xSe$ alloys 92 (1988) 445
Ard, C.K., see Capper 92 (1988) 1
Ashida, M., see Yanagi 92 (1988) 498

Bailey, R.T., see Holt 92 (1988) 239
Balestrino, G., U. Gambardella, Y.L. Liu, M. Marinelli, A. Paoletti, P. Paroli and G. Paternò, Growth of thick single crystals of the high T_c superconductor $Bi_2Sr_2CaCu_2O_{8+x}$ 92 (1988) 674
Barnett, S.A., see Hultman 92 (1988) 639
Bauer, G., see Ortner 92 (1988) 69
Benamar, M., Ph. Bouissou and P. Pelce, An exact solution for the shape of a crystal growing in a forced flow 92 (1988) 97
Bendraoui, A., see Harrous 92 (1988) 423
Bennema, P., see Hottenhuis 92 (1988) 171
Bennema, P., see Cherepanova 92 (1988) 671
Benyon, W., see Knight 92 (1988) 659
Berry, A.D., R.T. Holm, E.J. Cukauskas, M. Fatemi, D.K. Gaskill, R. Kaplan and W.B. Fox, Growth of superconducting thin films of bismuth–strontium–calcium–copper oxide by organometallic chemical vapor deposition 92 (1988) 344
Biloni, H., see De Cheveigné 92 (1988) 616
Boerhof, J., see Cherepanova 92 (1988) 671
Boerrigter-Lammers, H.J.M., see Van't Blik 92 (1988) 165
Bohr, H., N.E. Dam, I. Johannsen, F. Kragh and S. Petersen, Phase structures of high-T_c superconducting BiCaSrCuO ceramic and single crystal materials in SEM studies 92 (1988) 354
Bouissou, Ph., see Benamar 92 (1988) 97
Bouix, J., see Vincent 92 (1988) 553
Bradley, D.C., M.M. Faktor, D.M. Frigo and L.M. Smith, The volatilities of some adducts of trimethylindium 92 (1988) 37
Brandle, C.D., see Ikeda 92 (1988) 271
Brown, N., Effect of calcium ions on agglomeration of Bayer aluminium trihydroxide 92 (1988) 26
Buchan, N.I., C.A. Larsen and G.B. Stringfellow, Mass spectrometric studies of trimethylindium pyrolysis 92 (1988) 591
Buchan, N.I., C.A. Larsen and G.B. Stringfellow, A mass spectrometric study of the simultaneous reaction mechanism of TMIn and PH_3 to grow InP 92 (1988) 605
Bulsari, A.B., M.E. Orazem and J.G. Rice, The influence of axial diffusion on convective heat and mass transfer in a horizontal CVD reactor 92 (1988) 294

Cadoret, M., see Harrous 92 (1988) 423
Cadoret, R., see Harrous 92 (1988) 423
Camel, D., see Vahlas 92 (1988) 253
Campisi, G.G., see Henry 92 (1988) 348
Capper, P., I.G. Gale, F. Grainger, J.A. Roberts, C.L. Jones, J.J.G. Gosney, I. Kenworthy, C.K. Ard and W.G. Coates, Impurity segregation in $Cd_xHg_{1-x}Te$ crystals grown using ACRT 92 (1988) 1
Carlson, D.J., see Lin 92 (1988) 53
Chang, S.Y., K.-L. Hsueh, J. Gong and J.C. Lin, Application of tie-line concept on the liquid phase epitaxial growth of GaInAsP on InP 92 (1988) 454
Chaput, L., see Harrous 92 (1988) 423
Chen, S.C., Y.K. Su and F.S. Juang, Characterization and growth of $Al_{0.065}Ga_{0.935}Sb$ by liquid phase epitaxy 92 (1988) 118
Cherepanova, T.A., A.V. Vaivods, P. Bennema, M. Elwenspoek and J. Boerhof, Determination of the anisotropy of crystal growth rate from time dependent crystal growth forms 92 (1988) 671
Chernov, A.A. and A.I. Malkin, Regular and irregular growth and dissolution of (101) ADP faces under low supersaturations 92 (1988) 432
Chieux, P., see Dunn 92 (1988) 233
Choochon Lee, see Hyeon-Soo Kim 92 (1988) 77
Chopra, M.A., M.E. Glicksman and N.B. Singh, Measurement of the diffusion coefficient of acetone in succinotrile at its melting point 92 (1988) 543

Clapham, L. and R.W. Smith, Segregation behaviour of strontium in modified and unmodified Al–Si alloys 92 (1988) 263
Coates, W.G., see Capper 92 (1988) 1
Colabella, J.M., R.A. Stall and C.T. Sorenson, The adsorption and subsequent oxidation on AsH_3 and PH_3 on activated carbon 92 (1988) 189
Cook, E.L., see Radcliffe 92 (1988) 581
Cukauskas, E.J., see Berry 92 (1988) 344
Cukauskas, E.J., see Henry 92 (1988) 348
Cutting, J.F., see Radcliffe 92 (1988) 581

Dam, N.E., see Bohr 92 (1988) 354
De Bruyn, P.L., see Holt 92 (1988) 239
De Cheveigné, S., C. Guthmann, P. Kurowski, E. Vicente and H. Biloni, Directional solidification of metallic alloys: the nature of the bifurcation from planar to cellular interface 92 (1988) 616
De Keijser, M., C. van Opdorp and C. Weber, Peculiar asymmetric flow pattern in a vertical axisymmetric VPE reactor 92 (1988) 33
Debegnac, H., see Launay 92 (1988) 323
Delametter, C.N., see Lambropoulos 92 (1988) 390
Denes, L.J., see Singh 92 (1988) 13
Deng Peizhen, Qiao Jingwen, Hu Bing, Zhou Yongzong and Zhang Meizhen, Perfection and laser performances of Nd : YAG crystals grown by temperature gradient technique (TGT) 92 (1988) 276
Dobson, P.S., see Nouruzi-Kohrasani 92 (1988) 208
Dodson, B.W., The effect of Cottrell locking on structural stability in strained-layer semiconductor alloy structures 92 (1988) 222
Dore, J.C., see Dunn 92 (1988) 233
Drake, M,C., see Radcliffe 92 (1988) 581
Duffar, T., C. Potard and P. Dusserre, Growth analysis of the InSb compound by a calorimetric method in microgravity; results of the Spacelab-D1 experiment 92 (1988) 467
Dunn, M., J.C. Dore and P. Chieux, Structural studies of ice formation in porous silicas by neutron diffraction 92 (1988) 233
Dusserre, P., see Duffar 92 (1988) 467

Elwenspoek, M., see Cherepanova 92 (1988) 671
Eustathopoulos, N., see Vahlas 92 (1988) 253

Faktor, M.M., see Bradley 92 (1988) 37
Fang Dacheng and A. Hellawell, The surface morphology of crystals melting under solutions of different densities 92 (1988) 364
Fatemi, M., see Berry 92 (1988) 344
Fleming, J.G., Growth of FeS_2 (pyrite) from Te melts 92 (1988) 287
Fox, W.B., see Berry 92 (1988) 344
Fratello, V.J., see Ikeda 92 (1988) 271
Frigo, D.M., see Bradley 92 (1988) 37
Fulop, V., see Halász 92 (1988) 692

Gale, I.G., see Capper 92 (1988) 1
Gambardella, U., see Balestrino 92 (1988) 674
Gardeniers, J.G.E., see Hottenhuis 92 (1988) 171
Garman, D.M., see Yoel 92 (1988) 657
Gaskill, D.K., see Berry 92 (1988) 344
Glicksman, M.E., see Chopra 92 (1988) 543
Gong, J., see Chang 92 (1988) 454
Gosney, J.J.G., see Capper 92 (1988) 1
Gottlieb, M., see Singh 92 (1988) 13
Grainger, F., see Capper 92 (1988) 1
Gray, R.T., M.F. Larrousse and W.R. Wilcox, Diffusional decay of striations 92 (1988) 530
Greene, J.E., see Hultman 92 (1988) 639
Guang Weiyan, see Ren Zhifeng 92 (1988) 677
Guerrero, E., M. Quintero and J.C. Woolley, Phase relations in $(CuIn)_x(AgIn)_yCd_{2z}Te_2$ alloys 92 (1988) 150
Guthmann, C., see De Cheveigné 92 (1988) 616

Halász, I., V. Fulop, I. Kirschner and T. Porjesz, Thermoanalytical and X-ray diffraction investigations of $Ba_2Cu_3O_{5+d}$ for preparation of Y–Ba–Cu–O superconductors (E) 92 (1988) 692
Haneda, H., M. Isobe, A. Watanabe and S. Shirasaki, Single crystal growth of $(Mg_{1-x}Fe_x)(Al_{1-y}Fe_y)_2O_4$ solid solutions and their Mössbauer effect 92 (1988) 155
Harries, J.E., see Holt 92 (1988) 239
Harrous, M., L. Chaput, A. Bendraoui, M. Cadoret, C. Pariset and R. Cadoret, Phosphine and arsine decomposition in CVD reactors for InP and InGaAs growth 92 (1988) 423
Hase, U., see Kuwano 92 (1988) 17
Hasnain, S.S., see Holt 92 (1988) 239
Hayashi, S., see Yanagi 92 (1988) 498
Hellawell, A., see Fang Dacheng 92 (1988) 364
Henry, R.L., E.J. Cukauskas, S.B. Qadri, P.H. Klein and G.G. Campisi, Thin film growth of $YBa_2Cu_3O_7$ by spray-pyrolysis 92 (1988) 348
Higuchi, M., A. Takeuchi and K. Kodaira, Hydrothermal growth of calcite single crystals from H_2O–CO_2–$CaCO_3$ system 92 (1988) 341
Hiramatsu, K., see Tanaka 92 (1988) 311
Hirayama, N., see Ohshima 92 (1988) 461
Hjellming, L.N. and J.S.Walker, Mass transport in a Czochralski crystal puller with an axial magnetic field: melt motion due to crystal growth and buoyancy 92 (1988) 371
Holm, R.T., see Berry 92 (1988) 344
Holt, C., M.J.J.M. van Kemenade, J.E. Harries, L.S. Nelson, R.T. Bailey, D.W.L. Hukins, S.S. Hasnain and P.L. de Bruyn,

Preparation of amorphous calcium-magnesium phosphates at pH 7 and characterization by X-ray absorption and Fourier transform infrared spectroscopy 92 (1988) 239
Hottenhuis, M.H.J., J.G.E. Gardeniers, L.A.M.J. Jetten and P. Bennema, Potassium hydrogen phthalate: relation between crystal structure and crystal morphology 92 (1988) 171
Hottenhuis, M.H.J. and A. Oudenampsen, Fe^{3+} and Ce^{3+} acting as competitive impurities in the crystallization process of potassium hydrogen phthalate from solutions 92 (1988) 513
Hsieh, S.J., see Macrander 92 (1988) 83
Hsueh, K.-L., see Chang 92 (1988) 454
Hu Bing, see Deng Peizhen 92 (1988) 276
Huang, K.H. and B.W. Wessels, Growth and properties of InAsP alloys prepared by organometallic vapor phase epitaxy 92 (1988) 547
Hukins, D.W.L., see Holt 92 (1988) 239
Hultman, L., S.A. Barnett, J.-E. Sundgren and J.E. Greene, Growth of epitaxial TiN films deposited on MgO(100) by reactive magnetron sputtering: the role of low-energy ion irradiation during deposition 92 (1988) 639
Hyeon-Soo Kim, Sik-ki Min and Choochon Lee, Indium content measurement and influence on etch pit density of VPE grown $In_xGa_{1-x}As(x < 0.03)/GaAs$ epilayers 92 (1988) 77
Hyeon-Soo Kim, Yong Kim, Moo-Sung Kim and Suk-Ki Min, Structural properties of GaAs grown on (100) Si substrates by MOCVD 92 (1988) 507
Hyung Yong Ra, see Seong Gyoon Kim 92 (1988) 629

Ikeda, J.A.S., V.J. Fratello and C.D. Brandle, Viscosity and density measurements of molten lithium niobate 92 (1988) 271
Ishizawa, Y., see Otani 92 (1988) 8
Ishizawa, Y., see Otani 92 (1988) 359
Isobe, M., see Haneda 92 (1988) 155

Jetten, L.A.M.J., see Hottenhuis 92 (1988) 171
Jiang Yandao, see Ren Zhifeng 92 (1988) 677
Johannsen, I., see Bohr 92 (1988) 354
Jones, C.L., see Capper 92 (1988) 1
Juang, F.S., see Chen 92 (1988) 118

Kaplan, R., see Berry 92 (1988) 344
Kenworthy, I., see Capper 92 (1988) 1
Klein, R.H., see Henry 92 (1988) 348
Kimura, M., see Sukegawa 92 (1988) 46
Kirschner, I., see Halász 92 (1988) 692
Knight, D.G. and W. Benyon, InGaAsP/InP distributed feedback laser wafers grown by an interrupted liquid phase epitaxy technique 92 (1988) 659
Kobayashi, M., see Takekawa 92 (1988) 687
Kobayashi, S., Numerical analysis of oxygen transport in magnetic Czochraslki growth of silicon (E) 92 (1988) 692
Kodaira, K., see Higuchi 92 (1988) 341
Kosuda, K., see Takekawa 92 (1988) 687
Koukitu, A., S. Simamura, H. Nakai, T. Suzuki and H. Seki, The VPE growth of InGaP by the single flat temperature zone method 92 (1988) 316
Koyama, T., see Yodo 92 (1988) 196
Kragh, F., see Bohr 92 (1988) 354
Kunjomana, A.G. and E. Mathai, Growth and dislocation density of $Te_{1-x}Se_x$ whiskers 92 (1988) 666
Kurowski, P., see De Cheveigné 92 (1988) 616
Kuwano, Y., S. Saito and U. Hase, Crystal growth and optical properties of Nd:GCAG 92 (1988) 17

Lal, R., see Hak-Do Yoo 92 (1988) 101
Lambropoulos, J.C. and C.N. Delametter, The effect of interface shape on thermal stress during Czochralski crystal growth 92 (1988) 390
Larrousse, M.F., see Gray 92 (1988) 530
Larsen, C.A., see Buchan 92 (1988) 591
Larsen, C.A., see Buchan 92 (1988) 605
Launay, J.C., H. Debegnac, B. Zappoli and C. Mignon, Germanium epitaxial growth in closed ampoules. I. Experimental results – 1D modelling 92 (1988) 323
Lefaucheux, F., see Andreazza 92 (1988) 415
Lehoczky, S.L., see Andrews 92 (1988) 445
Li Qingchun, see Xu Daming 92 (1988) 663
Lin, C.T., D.J. Carlson and A.F. Witt, Growth related residual strain in LEC GaAs 92 (1988) 53
Lin, J.C., see Chang 92 (1988) 454
Liu, Y.L., see Balestrino 92 (1988) 674
López-Acevedo, V., see Prieto 92 (1988) 61
López-Andrés, S., see Prieto 92 (1988) 61

Machida, K., see Nakajima 92 (1988) 23
Macrander, A.T., S.J. Hsieh, F. Ren and J.S. Patel, Electrical and structural characterization of highly perfect semi-insulating InAlAs grown by molecular beam epitaxy 92 (1988) 83
Maeda, S., see Yanagi 92 (1988) 498
Malkin, A.I., see Chernov 92 (1988) 432
Mariella, Jr., R., see Aina 92 (1988) 215
Marinelli, M., see Balestrino 92 (1988) 674
Mariolacos, K., Synthese von CuJ-Einkristallen im Temperaturgefälle – eine thermodynamische Betrachtung 92 (1988) 332
Martín-Vivaldi, J.L., see Prieto 92 (1988) 61
Mathai, E., zee Kunjomana 92 (1988) 666
Mattingly, M., see Aina 92 (1988) 215
Mazelsky, R., see Singh 92 (1988) 13

Melas, A., see Aina 92 (1988) 215
Menard, J.C., see Nicolau 92 (1988) 128
Mignon, C., see Launay 92 (1988) 323
Miller, L.R., see Radcliffe 92 (1988) 581
Moo-Sung Kim, see Hyeon-Soo Kim 92 (1988) 507
Mousa, M.A. and M.A. Ahmed, Crystallization kinetics of amorphous $Ge_{20}Se_5Te_{75}$ 92 (1988) 259
Mutaftschiev, B., see Andreazza 92 (1988) 415

Nae Eung Lee, see Seong Gyoon Kim 92 (1988) 629
Nakai, H., see Koukitu 92 (1988) 316
Nakajima, K. and K. Machida, Thermal expansion of gallium garnets and Bi-substituted iron garnet epitaxial thick films 92 (1988) 23
Nandapurkar, P. and D.R. Poirier, Heat of mixing and morphological stability 92 (1988) 88
Nelson, L.S., see Holt 92 (1988) 239
Neumann, G. and K.-H. Zschauer, Hydrodynamic description of vapour levitation epitaxy 92 (1988) 397
Nickel, S., see Reier 92 (1988) 335
Nicolau, Y.F. and J.C. Menard, Solution growth of ZnS, CdS and $Zn_{1-x}Cd_xS$ thin films by the successive ionic-layer adsorption and reaction process; growth mechanism 92 (1988) 128
Nomura, S., H. Yoshino and K. Ando, Phase diagram of the system $YBa_2Cu_3O_{7-\delta}$–$BaCuO_2 \cdot CuO$ 92 (1988) 682
Nouruzi-Khorasani, A. and P.S. Dobson, An electron microscope study of defects in Cr-doped CdTe 92 (1988) 208
Nozaki, H., see Takekawa 92 (1988) 687

Ohsaka, K. and E.H. Trinh, On dendritic growth in undercooled melts 92 (1988) 338
Ohshima, M. and N. Hirayama, LPE growth of InP/InGaAsP multilayers using a horizontal sliding boat with multi-melt containers 92 (1988) 461
Orazem, M.E., see Bulsari 92 (1988) 294
Ortner, B. and G. Bauer, (111) CdTe epitaxy on (100) GaAs substrates 92 (1988) 69
Otani, S., T. Tanaka and Y. Ishizawa, Growth conditions of high purity TiC single crystal using the floating zone method 92 (1988) 8
Otani, S., T. Tanaka and Y. Ishizawa, Effect of W doping on the growth of TiC crystal by the floating zone method 92 (1988) 359
Oudenampsen, A., see Hottenhuis 92 (1988) 513

Paoletti, A., see Balestrino 92 (1988) 674
Pariset, C., see Harrous 92 (1988) 423
Paroli, P., see Balestrino 92 (1988) 674
Patel, J.S., see Macrander 92 (1988) 83
Paternò, G., see Balestrino 92 (1988) 674
Pelce, P., see Benamar 92 (1988) 97
Petersen, S., see Bohr 92 (1988) 354
Plyatsko, S.V., see Sizov 92 (1988) 571
Poirier, D.R., see Nandapurkar 92 (1988) 88
Ponthenier, J.-L., see Vincent 92 (1988) 553
Porjesz, T., see Halász 92 (1988) 692
Potard, C., see Duffar 92 (1988) 467
Prieto, M., C. Viedma, V. López-Acevedo, J.L. Martín-Vivaldi and S. López-Andrés, Mass-transfer and supersaturation in crystal growth in gels; application to $CaSO_4 \cdot 2H_2O$ 92 (1988) 61

Qadri, S.B., see Henry 92 (1988) 348
Qiao Jingwen, see Deng Peizhen 92 (1988) 276
Quintero, M., see Guerrero 92 (1988) 150

Radcliffe, M.D., J.E. Steffen, E.L. Cook, J.F. Cutting, L.R. Miller, M.C. Drake, F.S. Schroder and J. Stevens, Organic crystal growth in low earth orbit 92 (1988) 581
Reier, F.W., S. Nickel and H. Schumann, On the detectibility of oxygen traces in trimethylindium by mass spectrometry 92 (1988) 335
Ren, F., see Macrander 92 (1988) 83
Ren Zhifeng, Yan Xiuli, Jiang Yandao and Guan Weiyan, Growth of superconducting single crystals of composition Bi : Sr : Ca : Cu = 2 : 2 : 1 : 2 in the Bi–Sr–Ca–Cu–O system 92 (1988) 677
Rice, J.G., see Bulsari 92 (1988) 294
Roberts, J.A., see Capper 92 (1988) 1

Saito, S., see Kuwano 92 (1988) 17
Samarasekera, I.V., see Schvezov 92 (1988) 479
Samarasekera, I.V., see Schvezov 92 (1988) 489
Schönherr, E., The investigation of the Pizzarello method with the theory of systems 92 (1988) 123
Schroder, F.S. see Radcliffe 92 (1988) 581
Schvezov, C.E., I.V. Samarasekera and F. Weinberg, Calculation of the shear stress distribution in LEC gallium arsenide for different growth conditions 92 (1988) 479
Schvezov, C.E., I.V. Samarasekera and F. Weinberg, Calculation of the thermal and stress fields in LEC gallium arsenide after separation from the melt 92 (1988) 489
Seki, H., see Koukitu 92 (1988) 316
Seong Gyoon Kim, Nae Eung Lee and Hyung Yong Ra, Dendritic growth of α(Fe, Si) ferrite in annealed $Fe_{80}Si_8B_{12}$ metallic glass 92 (1988) 629
Shirasaki, S., see Haneda 92 (1988) 155
Simamura, S., see Koukitu 92 (1988) 316
Singh, N.B., L.J. Denes, M. Gottlieb and R. Mazelsky, Growth and characterization of large Tl_3AsSe crystals for collinear AOTF devices 92 (1988) 13

Singh, N.B., see Chopra 92 (1988) 543
Sizov, F.F. and S.V. Plyatsko, Homogeneity range and nonstoichiometric defects in IV–VI narrow-gap semiconductors 92 (1988) 571
Schumann, H., see Reier 92 (1988) 335
Smith, L.M., see Bradley 92 (1988) 37
Smith, R.W., see Clapham 92 (1988) 263
Sorenson, C.T., see Colabella 92 (1988) 189
Stall, R.A., see Colabella 92 (1988) 189
Steffen, J.E., see Radcliffe 92 (1988) 581
Steinhauser, S., see Aina 92 (1988) 215
Stevens, J., see Radcliffe 92 (1988) 581
Stringfellow, G.B., see Buchan 92 (1988) 591
Stringfellow, G.B., see Buchan 92 (1988) 605
Su, Y.K., see Chen 92 (1988) 118
Sukegawa, T., M. Kimura and A. Tanaka, Gravity effect on dissolution and growth of silicon in the In–Si system 92 (1988) 46
Suk-Ki Min, see Hyeon-Soo Kim 92 (1988) 77
Suk-Ki Min, see Hyeon-Soo Kim 92 (1988) 507
Sundgren, J.-E., see Hultman 92 (1988) 639
Suzuki, T., see Koukitu 92 (1988) 316
Suzuki, T., Thermal convection in a horizontal magnetic field 92 (1988) 407
Szofran, F.R., see Andrews 92 (1988) 445

Takekawa, S., H. Nozaki, A. Umezono, K. Kosuda and M. Kobayashi, Single crystal growth of the superconductor $Bi_{2.0}$-$(Bi_{0.2}Sr_{1.8}Ca_{1.0})Cu_{2.0}O_8$ 92 (1988) 687
Takeuchi, A., see Higuchi 92 (1988) 341
Tanaka, A., see Sukegawa 92 (1988) 46
Tanaka, S., N. Amano, K. Hiramatsu and I. Akasaki, A verification of immiscibility in InGaAsP quaternary alloys 92 (1988) 311
Tanaka, T., see Otani 92 (1988) 8
Tanaka, T., see Otani 92 (1988) 359
Thomas, T.L., see Yoel 92 (1988) 657
Trinh, E.H., see Ohsaka 92 (1988) 338
Tobisawa, S., see Yamada 92 (1988) 143
Trolinger, J.D., see Yoo 92 (1988) 101

Umezono, A., see Takekawa 92 (1988) 687

Vahlas, C., N. Eustathopoulos and D. Camel, Adsorption-induced solid–liquid interfacial roughening in Zn alloys 92 (1988) 253
Vaivods, A.V., see Cherepanova 92 (1988) 671
Van Kemenade, M.J.J.M., see Holt 92 (1988) 239
Van Opdorp, C., see De Keijser 92 (1988) 33
Van 't Blik, H.F.J. and H.J.M. Boerrigter-Lammers, On the MOVPE growth of self-aligned laser structures 92 (1988) 165
Vicente, E., see De Cheveigné 92 (1988) 616
Viedma, C., see Prieto 92 (1988) 61
Vincent, H., J.-L. Ponthenier et J. Bouix, CVD réactive de SiC sur graphite; comparaison entre résultats expérimentaux et prévisions thermodynamiques 92 (1988) 553

Walker, J.S., see Hjellming 92 (1988) 371
Watanabe, A., see Haneda 92 (1988) 155
Weber, C., see De Keijser 92 (1988) 33
Weinberg, F., see Schvezov 92 (1988) 479
Weinberg, F., see Schvezov 92 (1988) 89
Wessels, B.W., see Huang 92 (1988) 547
Wilcox, W.R., see Hak-Do Yoo 92 (1988) 101
Wilcox, W.R., see Gray 92 (1988) 530
Witt, A.F., see Lin 92 (1988) 53
Woolley, J.C., see Guerrero 92 (1988) 150

Xu Daming and Li Qingchun, Solute redistribution manners under different types of programmed freezing rates during Bridgman growth 92 (1988) 663

Yamada, K. and S. Tobisawa, Morphology of carbon particles formed by the conically converging shock-wave technique 92 (1988) 143
Yamashita, K., see Yodo 92 (1988) 196
Yan Xiuli, see Ren Zhifeng 92 (1988) 677
Yanagi, H., S. Maeda, S. Hayashi and M. Ashida, Crystal growth of octacyanometalphthalocyanine–metal complexes in thin films 92 (1988) 498
Yodo, T., T. Koyama and K. Yamashita, Dependence of source gas mole ratio on crystalline quality of ZnSe layers grown on (100) ZnSe substrates by atmospheric pressure metalorganic vapor phase epitaxy 92 (1988) 196
Yoel, D.W., T.L. Thomas and D.M. Garman, Two-wall fused-silica ampoules for crystal growth 92 (1988) 657
Yong Kim, see Hyeon-Soo Kim 92 (1988) 507
Yoo, Hak-Do, W.R. Wilcox, R. Lal and J.D. Trolinger, Modelling of growth of triglycine sulphase crystals in Spacelab 3 92 (1988) 101
Yoshino, H., see Nomura 92 (1988) 682

Zappoli, B., see Launay 92 (1988) 323
Zhang Meizhen, see Deng Peizhen 92 (1988) 276
Zhou Yongzong, see Deng Peizhen 92 (1988) 276
Zschauer, K.-H., see Neumann 92 (1988) 397

Journal of Crystal Growth 92 (1988) 698–701
North-Holland, Amsterdam

SUBJECT INDEX

Accelerated crucible rotation technique 1, 530
Accousto-optic tunable filter 13
Adducts 37
Adsorption 128, 189, 253, 263, 323, 432, 513
Alloys 88, 253, 263, 364, 616, 663
Aluminum
– alloys 616
– copper alloys 663
– gallium antimonide 118
– gallium arsenide 165
– hydroxide 26
– silicon alloy 263
Ammonium
– dihydrogen phosphate 415, 432
Apparatus
– for solution growth
– – by flux
– – – of bismuth calcium strontium cuprate 677
– – by low temperature
– – – under microgravity
– – – – of organic crystals 581
– for thin film growth
– – by liquid phase epitaxy
– – – by cyclic temperature process
– – – – of silicon 46
– – – for multilayer growth
– – – – of III–V compounds 461
– – – using an interrupted technique
– – – of indium gallium arsenide phosphide 659
– – by vapor levitation epitaxy
– – – hydrodynamic description of 397
– – by vapor phase epitaxy
– – – by chemical vapor deposition
– – – – of silicon carbide 553
– – – by single flat temperature zone
– – – – of indium gallium phosphide 316
– for vapor growth
– – by evaporation and condensation
– – – of carbon 143
– for miscellaneous purposes
– – chemical vapor deposition using inclined susceptor 294
– – crystal growth – two-wall fused-silica ampoules 657
– – measuring viscosity of melt in Czochralski growth 271
– – modified entrainment method (MEM) 37
– – scrubbing metalorganic chemical vapor deposition effluent 189

Barium
– copper oxide 692
Bismuth
– calcium strontium copper oxide 344, 354, 674, 677, 687
– organic 344
Boundary layer control 294, 581
Brushite 239
Buoyancy effects 371, 407

Cadmium
– mercury telluride 1
– sulphide 128
– telluride 69, 150, 208
Calcite 341
Calcium
– carbonate 341
– organic 344
– phosphate dihydrate 239
– sulphate dihydrate 61
Carbon 143
Cellular growth
– in alloys 616
– of bismuth strontium calcium copper oxide 687
Characterization methods
– by absorption spectroscopy 17
– by atomic adsorption spectrometry 1, 61, 263
– by Auger electron spectroscopy 454
– by carbon analysis 359
– by density measurements 271, 445
– by differential thermal analysis 150, 259, 677, 682, 692
– by electrical methods 83, 128, 215, 259, 316, 344, 348, 547, 571, 677, 687
– by electron microscopy 26, 46, 118, 128, 143, 208, 239, 323, 341, 344, 348, 354, 498, 507, 553, 629, 639, 682
– by electron probe microanalysis 23, 118, 276, 359, 687
– by electron spectroscopy for chemical analysis 553
– by extended X-ray absorption fine structure 239
– by Fourier transform infrared 239, 454
– by holographic interferometry 101
– by inductively coupled plasma spectrometry 215, 513, 677
– by laser performance 276
– by magnetic properties 674, 677
– by mass spectrometry 1, 335, 591, 605
– by Mössbauer spectroscopy 155
– by neutron diffraction 155, 233
– by optical microscopy 8, 46, 77, 101, 196, 276, 341, 359, 364, 445, 513, 547, 581, 666, 671, 674, 687
– by optical properties 17
– by photoluminescence 77, 118, 196, 215, 311, 316, 547, 659
– by Raman spectroscopy 553
– by resistivity 692
– by secondary ion mass spectrometry 215, 461
– by thermal expansion 23

– by transmission spectroscopy 1, 13, 53, 445
– by viscosity of melt 271
– by visualization of flow pattern 33
– by X-ray techniques 1, 8, 23, 77, 83, 118, 150, 155, 196, 239, 259, 276, 287, 311, 316, 344, 348, 354, 359, 454, 461, 507, 547, 553, 674, 677, 682, 687, 692
Computer simulation 33, 101, 663, 692
Constitutional supercooling 88, 445, 616
Convection 33, 46, 97, 101, 294, 338, 364, 371, 407, 445, 467, 530, 581, 692
Copper
– indium, silver indium, cadmium telluride 150
– (I) iodide 332

Dendritic growth 338, 543, 629
Devices 13, 165, 276, 461, 659
Decalcium phosphate dihydrate 239
Diffusional control 61, 101, 294, 323, 364, 530, 543, 581, 629
Dislocations 8, 13, 53, 69, 77, 208, 222, 276, 359, 390, 432, 479, 489, 513, 639, 666
Dissolution 46, 101, 364, 432, 666
Distribution coefficient 1, 155, 263, 364, 445, 454, 513
Dopants 1, 17, 23, 53, 208, 263, 276, 359, 371, 467

Etching
– chemical 8, 13, 77, 118, 165, 208, 253, 359, 666
Eutectic growth 263

Ferrite
– α(Fe,Si) 629
Finite element method 294
Four–six (IV–VI) compounds 571

Gadolinium
– gallium aluminum garnet 17
– gallium garnet 23
Gallium
– arsenide 53, 165, 390, 479, 489, 507
Garnets 17, 23, 276
Germanium 323
– selenide telluride 259
Glass
– iron–silicon–boron 629
Grain boundary 359
Gypsum 61

Heat flow control 101, 445, 467, 479, 489
Heterojunction 165, 222, 461
Hydrodynamics 371, 397, 467, 692
– magnetic 407

Ice 233, 364
Impurity 1, 26, 118, 171, 215, 335, 371, 432, 513, 530, 663, 666, 692
Inclusions 276, 687
Indium
– aluminum arsenide 83
– antimonide 467
– arsenide phosphide 547
– gallium arsenide 77, 423
– gallium arsenide phosphide 311, 454, 461, 659
– gallium phosphide 316
– organic 37, 215, 335, 547, 591
– phosphide 215, 390, 423, 461, 605, 659
Interface 69, 88, 118, 128, 233, 253, 263, 364, 390, 432, 467, 479, 639, 659, 671
Iron
– disulphide 287
– silicon boron glass 629

Kinetics
– of dissolution 432
– of growth 8, 46, 101, 118, 128, 165, 171, 215, 259, 263, 316, 323, 338, 359, 423, 432, 445, 454, 479, 530, 547, 605, 629, 639, 663, 671
– of interface control 271, 467, 581, 671
– of melting 364
– of nucleation 165, 415, 581
– of pyrolysis 591

Lasers 17, 165, 276, 659
Lattice mismatch 23, 69, 83, 128, 222, 311, 316, 454
Lead 364
– alloys 616
– tin selenide 571
– tin telluride 571
Lithium
– niobate 271

Magnesium
– aluminate 155
Mathematical model 88, 97, 294, 397, 467, 671
Melt growth technique
– by Bridgman–Stockbarger method
– – of IV–VI compounds 571
– – of indium antimonide 467
– – of mercury cadmium selenide 445
– – of mercury cadmium telluride 1
– – of thallium arsenide selenide (Tl_3AsSe_3) 13
– – solute redistribution during
– – – of alloys 663
– – using accelerated crucible rotation technique
– – – striations of 530
– by Czochralski method
– – of IV–VI compounds 571
– – of gadolinium gallium aluminum garnet 17
– – of gallium arsenide 53, 479, 489
– – of lithium niobate 271
– – of silicon 390, 692
– – of III–V compounds 390
– – under magnetic field
– – – of silicon 371
– – theory of 692
– by floating zone method

– – of bismuth strontium calcium copper oxide 687
– – of magnesium aluminate 155
– – of titanium carbide 8, 359
– by solvent evaporation
– – of cadmium telluride 208
– by temperature gradient technique
– – of yttrium aluminum garnet 276
– by uniaxial solidification
– – of aluminum silicon alloy 263
– – of binary alloys 88
– – theory of 88
Mercury
– cadmium selenide 445
– cadmium telluride 1
Metal
– complex 498
Microgravity 101, 294, 323, 338, 467, 581
Modified entrainment method (MEM) 37
Morphological stability 88, 222, 338, 616, 629
Morphology of growth 13, 26, 77, 97, 101, 128, 143, 171, 196, 233, 253, 263, 276, 287, 332, 338, 341, 498, 513, 553, 581, 629, 639, 666, 671

Nucleation 165, 415, 581, 666
Numbers
– Biot 390
– Damköhler 397
– Grashof 46, 101, 467
– Lewis 323
– Marangoni 467
– Peclet 97, 323, 338, 371, 397, 467
– Reynolds 294, 397, 467
– Sherwood 101, 397

Organic alloys 616
Organic crystals 101, 171, 338, 498, 513, 543, 581, 616, 671

Particle size distribution 26
Perfection of crystals 17, 53, 69, 83, 208, 276, 354, 390, 445, 507, 571, 581, 639
Periodic bond chain theory 171
Phase diagrams 150, 253, 364, 445, 454, 571, 677, 682
Phenomenological theory 581, 616, 629
Potassium
– hydrogen phthalate 171, 513
Precursor 335, 547, 591, 605
Purification of materials 1, 8
Pyrite 287

Quantum wells/size effects 165

Rare earth
– iron garnets 23

Segregation 263, 445, 467
Silicon 372, 390, 692
– carbide 553
Solid growth technique
– by melt and anneal technique
– – of bismuth calcium strontium cuprate 354
– – of copper indium, silver indium, cadmium telluride 150
– – of germanium selenide telluride 259
– – of metallic glass 629
– – of zinc lead (tin) alloy 253
– by solid state reaction
– – of barium copper oxide 692
– – of thallium barium copper oxide 692
Solution growth technique
– by bulk crystallization
– – of aluminum hydroxide 26
– by flux method
– – of bismuth calcium strontium copper oxide 674, 677
– – of pyrite 287
– – of yttrium barium copper oxide 682
– by gel method
– – of ammonium dihydrogen phosphate 415
– – of gypsum 61
– by hydrothermal method
– – of calcite 341
– by low temperature method
– – of ammonium dihydrogen phosphate 432
– – of brushite 239
– – of ice 233
– – of potassium hydrogen phthalate 171, 513
– – of triglycine sulphate 101
– – under microgravity
– – – of organic crystals 581
Spinel 155, 639
Statistical mechanics, molecular theory 629
Stefan problem or moving boundary problem 101, 338, 467
Step 666
Strain 53, 222, 276, 390, 432, 479, 489
Striations 530
Strontium
– organic 344
Succinonitrile 338, 543
Superconductivity 344, 348, 354, 674, 677, 682, 687, 692
– bulk 354, 674, 677, 682, 687
– ceramics 354
– characterization 344, 348, 354, 674, 677, 682, 687, 692
– crystal chemistry 344, 348, 674, 677, 682, 687
– high T_c 344, 348, 354, 674, 677, 682, 687, 692
– phase relationships 677, 682
– thin films 344, 348
Supercooling, supersaturation 61, 97, 118, 233, 323, 338, 432, 454, 659, 666, 671
Superlattices 222
Surface energy, determination of 432
Surface processes, theory 128
Surface structure 26, 196, 348, 364, 513, 671

Tellurium
– selenium 666
Thallium

– arsenide selenide 13
– barium copper oxide 692
Theory of systems 123
Thermodynamics 88, 253, 287, 316, 332, 338, 415, 445, 553, 571, 605
Thin film growth
– by liquid phase epitaxy
– – of aluminum gallium antimonide 118
– – of garnets 23
– – of indium gallium arsenide phosphide 311, 454, 461, 659
– – of indium phosphide 461, 659
– – of pyrite 287
– – of silicon 46
– by molecular beam epitaxy
– – of indium aluminum arsenide 83
– by solution epitaxy
– – of cadmium sulphide 128
– – of zinc cadmium sulphide 128
– – of zinc sulphide 128
– by spray pyrolysis epitaxy
– – of yttrium barium copper oxide 348
– by sputtering
– – of titanium nitride 639
– by vapor levitation epitaxy
– – hydrodynamic description of 397
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of indium gallium arsenide 77, 423
– – – of indium phosphide 423
– – – of silicon carbide 553
– – – using inclined susceptor
– – – – mathematical model of 294
– – through evaporation and condensation
– – – of carbon 143
– – – of organometallic complex 498
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 165
– – – of bismuth calcium strontium copper oxide 344
– – – of gallium arsenide 165, 507
– – – of indium arsenide phosphide 547
– – – of indium phosphide 215, 605
– – – of zinc selenide 196
– – – theory of 591
– – through single flat temperature zone
– – – of indium gallium phosphide 316
Three–five (III–V) compounds 222, 316, 390, 461, 605
Tin 364
Titanium
– carbide 8, 359
– nitride 639
Triglycine sulphate 101

Vapor growth technique
– by chemical transport
– – of copper(I) iodide 332
– by evaporation and condensation
– – of tellurium selenium 666
– by Pizzarello method
– – theory of 123
– flow visualization and simulation of 33

Whisker growth
– of tellurium selenium 666

Yttrium
– aluminum garnet 276
– barium copper oxide 348, 682, 692

Zinc
– cadmium sulphide 128
– lead (tin) alloy 253
– organic 196
– selenide 196
– sulphide 128